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Team Nexperia



PBSS4560PA

60 V, 6 A NPN low V_{CEsat} (BISS) transistor Rev. 1 — 19 May 2010

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5560PA.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|--------------|-----|-----|------|
| V_{CEO} | collector-emitter voltage | open base | - | - | 60 | V |
| I _C | collector current | | - | - | 6 | Α |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | - | 7 | Α |
| R _{CEsat} | collector-emitter saturation resistance | $I_C = 6 \text{ A};$ $I_B = 300 \text{ mA}$ | <u>[1]</u> - | 34 | 48 | mΩ |

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



2. Pinning information

Table 2. Pinning

| | • | | |
|-----|-------------|----------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | base | | |
| 2 | emitter | 3 | 3 |
| 3 | collector | | 1 — |
| | | 1 2 | sym021 |
| | | Transparent top view | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | Package | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PBSS4560PA | HUSON3 | plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 \times 2 \times 0.65 mm | SOT1061 | | | |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS4560PA | A8 |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

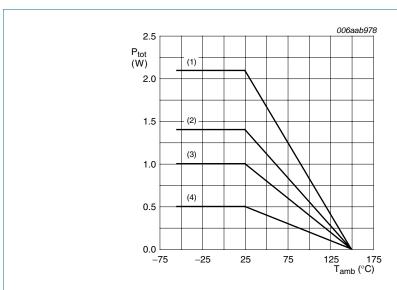
| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|--------------------------------------|--------------|-----|------|
| V_{CBO} | collector-base voltage | open emitter | - | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 60 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 6 | V |
| I _C | collector current | | - | 6 | Α |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 7 | Α |
| I _B | base current | | - | 600 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | <u>[1]</u> - | 500 | mW |
| | | | [2] - | 1 | W |
| | | | [3] _ | 1.4 | W |
| | | | [4] _ | 2.1 | W |

Table 5. Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|------------|-----|------|------|
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -55 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---|-------------|--------------|-----|-----|-----|------|
| $R_{th(j\text{-}a)} \qquad \text{thermal resistance from } \\ \text{junction to ambient}$ | in free air | <u>[1]</u> _ | - | 250 | K/W | |
| | | [2] | - | 125 | K/W | |
| | | | [3] | - | 90 | K/W |
| | | | [4] | - | 60 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- B] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

PBSS4560PA

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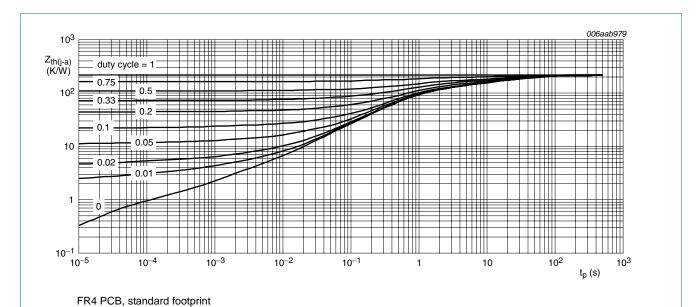


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

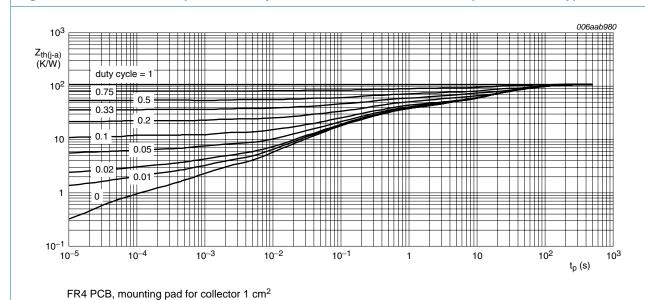


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

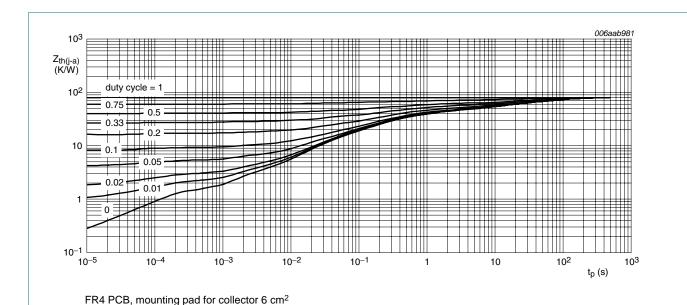
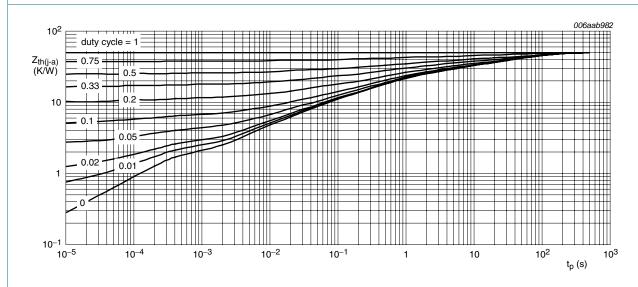


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

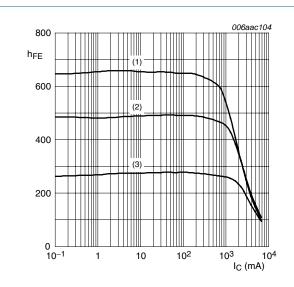
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|---|-------|------|-----|------|
| I _{CBO} | collector-base | $V_{CB} = 48 \text{ V}; I_E = 0 \text{ A}$ | - | - | 100 | nΑ |
| | cut-off current | $V_{CB} = 48 \text{ V}; I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$ | - | - | 50 | μА |
| I _{CES} | collector-emitter cut-off current | $V_{CE} = 48 \text{ V}; V_{BE} = 0 \text{ V}$ | - | - | 100 | nA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$ | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 2 V | [1] | | | |
| | | $I_C = 0.5 A$ | 280 | 440 | - | |
| | | I _C = 1 A | 260 | 420 | - | |
| | | I _C = 2 A | 210 | 325 | - | |
| | | I _C = 6 A | 70 | 120 | - | |
| V _{CEsat} | collector-emitter | $I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}$ | [1] - | 22 | 30 | mV |
| saturation voltage | saturation voltage | $I_C = 1 A; I_B = 50 mA$ | [1] - | 45 | 60 | mV |
| | | $I_C = 1 A$; $I_B = 10 mA$ | [1] - | 70 | 95 | mV |
| | | $I_C = 2 A$; $I_B = 20 mA$ | [1] - | 115 | 170 | mV |
| | | $I_C = 3 A$; $I_B = 30 mA$ | [1] - | 165 | 250 | mV |
| | | $I_C = 4 A$; $I_B = 400 \text{ mA}$ | [1] - | 130 | 200 | mV |
| | | $I_C = 6 A$; $I_B = 300 mA$ | [1] - | 200 | 290 | mV |
| R _{CEsat} | collector-emitter saturation resistance | $I_C = 6 \text{ A}; I_B = 300 \text{ mA}$ | [1] - | 34 | 48 | mΩ |
| V _{BEsat} | base-emitter | $I_C = 1 A; I_B = 10 mA$ | [1] - | 0.75 | 0.9 | V |
| | saturation voltage | $I_C = 6 \text{ A}; I_B = 300 \text{ mA}$ | [1] - | 0.97 | 1.1 | V |
| V_{BEon} | base-emitter turn-on voltage | $V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$ | [1] - | 0.75 | 0.9 | V |
| t _d | delay time | $V_{CC} = 9 \text{ V}; I_C = 2 \text{ A};$ | - | 22 | - | ns |
| t _r | rise time | $I_{Bon} = 0.1 \text{ A};$ $I_{Boff} = -0.1 \text{ A}$ | - | 101 | - | ns |
| t _{on} | turn-on time | I _{Boff} = -0.1 A | - | 123 | - | ns |
| t _s | storage time | | - | 635 | - | ns |
| t _f | fall time | | - | 145 | - | ns |
| t _{off} | turn-off time | | - | 780 | - | ns |
| f⊤ | transition frequency | $V_{CE} = 10 \text{ V};$ $I_{C} = 100 \text{ mA};$ $f = 100 \text{ MHz}$ | 90 | 150 | - | MHz |
| C _c | collector capacitance | $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz | - | 23 | 30 | pF |

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



- $V_{CE} = 2 V$
- (1) T_{amb} = 100 °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values

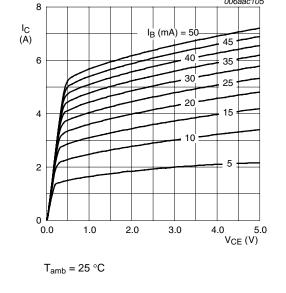
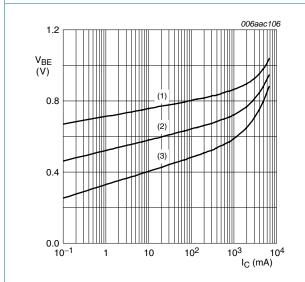
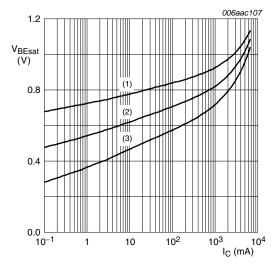


Fig 7. Collector current as a function of collector-emitter voltage; typical values



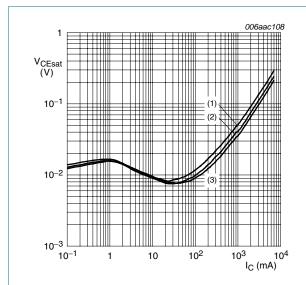
- $V_{CE} = 2 V$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 20$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



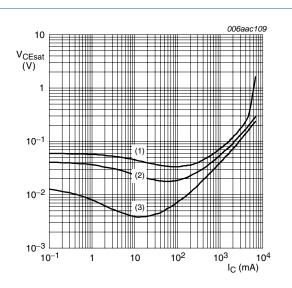
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

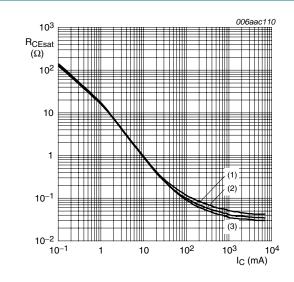


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3) $I_C/I_B = 10$

Fig 11. Collector-emitter saturation voltage as a function of collector current; typical values



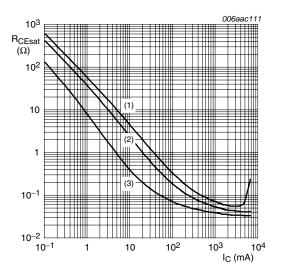
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values



T_{amb} = 25 °C

(1)
$$I_C/I_B = 100$$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 10$

Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

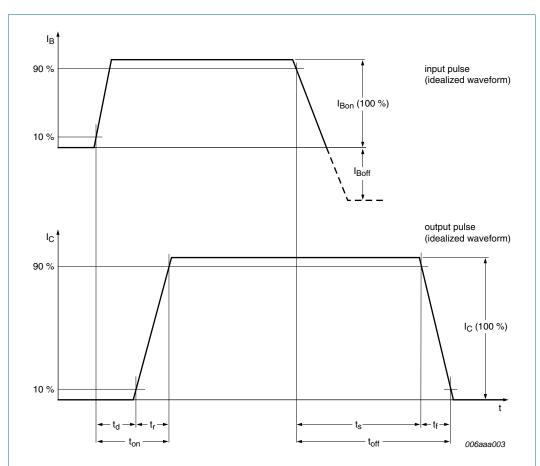
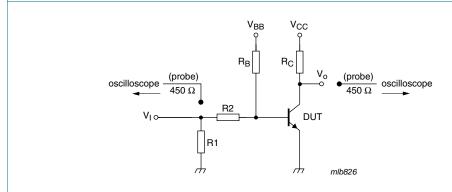
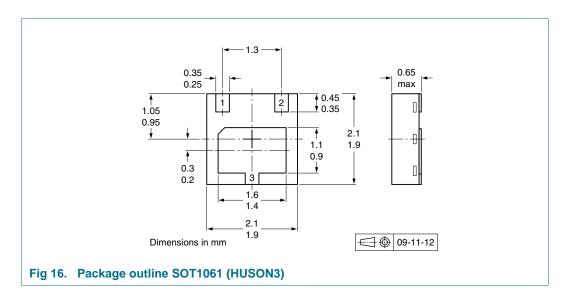


Fig 14. BISS transistor switching time definition



 $V_{CC}=9~V;~I_C=2~A;~I_{Bon}=0.1~A;~I_{Boff}=-0.1~A$ Fig 15. Test circuit for switching times

9. Package outline



10. Packing information

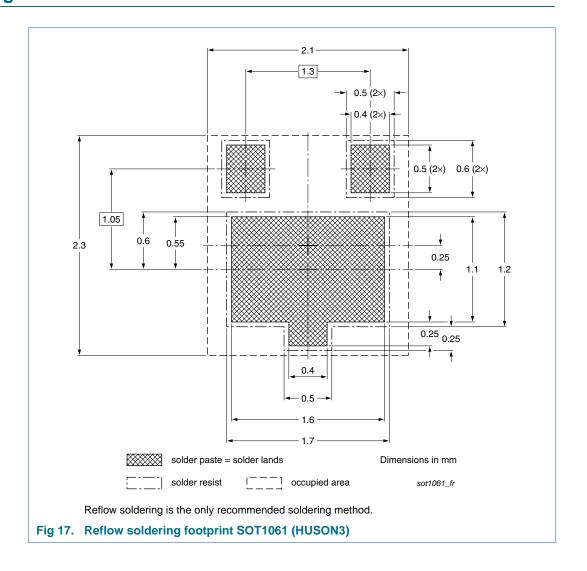
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packing quantity |
|-------------|---------|--------------------------------|------------------|
| | | | 3000 |
| PBSS4560PA | SOT1061 | 4 mm pitch, 8 mm tape and reel | -115 |

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering





12. Revision history

Table 9. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PBSS4560PA v.1 | 20100519 | Product data sheet | - | - |

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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PBSS4560PA

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NXP Semiconductors PBSS4560PA

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

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PBSS4560PA

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

15. Contents

| 1 | Product profile |
|------|---------------------------|
| 1.1 | General description |
| 1.2 | Features and benefits |
| 1.3 | Applications |
| 1.4 | Quick reference data 1 |
| 2 | Pinning information 2 |
| 3 | Ordering information |
| 4 | Marking 2 |
| 5 | Limiting values |
| 6 | Thermal characteristics 3 |
| 7 | Characteristics 6 |
| 8 | Test information 9 |
| 9 | Package outline |
| 10 | Packing information |
| 11 | Soldering 11 |
| 12 | Revision history 12 |
| 13 | Legal information |
| 13.1 | Data sheet status |
| 13.2 | Definitions |
| 13.3 | Disclaimers |
| 13.4 | Trademarks14 |
| 14 | Contact information 14 |
| 15 | Contents |

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